

2007 — FUJIWARA Yasufumi

Scientific Papers/Commentary Articles

1. Y. Fujiwara, S. Takemoto, K. Nakamura, K. Shimada, M. Suzuki, K. Hidaka, Y. Terai and M. Tonouchi, Ultrafast carrier-trapping in Er-doped and Er,O-codoped GaAs revealed by pump and probe technique, *Physica B*, 401-402, pp. 234-237, 2007
2. Y. Fujiwara, S. Takemoto, T. Tokuno, K. Hidaka, H. Ichida, M. Suzuki, Y. Terai, Y. Kanematsu and M. Tonouchi, Mechanism of excitation and relaxation in Er,O-codoped GaAs for 1.5mm light-emitting devices with extremely stable wavelength, *Physica Status Solidi (a)*, 205(1), pp. 64-67, 2007
3. Y. Fujiwara, K. Nakamura, S. Takemoto, J. Sugino, Y. Terai, M. Suzuki and M. Tonouchi, Direct observation of picosecond-scale energy-transfer processes in Er,O-codoped GaAs by pump-probe reflection technique, *Physics of Semiconductors*, AIP Conference Proceedings, Vol. 893, pp. 245-246, 2007
4. K. Shimada, Y. Terai, S. Takemoto, K. Hidaka, Y. Fujiwara, M. Suzuki and M. Tonouchi, Terahertz radiation from Er,O-codoped GaAs surface grown by organometallic vapor phase epitaxy, *Applied Physics Letters*, 92(11), pp. 111115-1-3, 2008
5. K. Yamaoka, N. Okada, Y. Yoshizako, Y. Terai and Y. Fujiwara, Influence of plasma gases on insulating properties of low-temperature deposited SiOCH films by remote plasma-enhanced chemical vapor deposition, *Japanese Journal of Applied Physics*, 46(4B), pp. 1997-2000, 2007
6. K. Yamaoka, Y. Terai, N. Okada, Y. Yamaguchi, Y. Yoshizako and Y. Fujiwara, Low temperature deposition of amorphous carbon films for surface passivation of carbon-doped silicon oxide, *Advanced Materials Research*, 26-28, pp. 645-648, 2007
7. Y. Terai, Y. Maeda and Y. Fujiwara, Nondestructive investigation of b-FeSi₂/Si interface by photoluminescence measurements, *Thin Solid Films*, 515(22), pp. 8129-8132, 2007
8. K. Yasutake, N. Tawara, H. Ohmi, Y. Terai, H. Kakiuchi, H. Watanabe and Y. Fujiwara, Characterization of epitaxial silicon films grown by atmospheric pressure plasma chemical vapor deposition using porous carbon electrode, *Japanese Journal of Applied Physics*, 46(4B), pp. 2510-2515, 2007
9. Y. Terai, T. Tokuno, H. Ichida, Y. Kanematsu and Y. Fujiwara, Electroluminescence properties of GaInP/GaAs:Er,O/GaInP double heterostructure light-emitting diodes at low temperature, *Optical Materials*, 印刷中, 2008
10. Y. Terai, K. Hidaka and Y. Fujiwara, Organometallic vapor phase epitaxy of Er,O-codoped GaAs using trisdipivaloylmethanatoerbium, *Journal of Physics Conference Series*, 印刷中, 2008
11. K. Fujii, K. Hidaka, D. Yamamoto, Y. Terai and Y. Fujiwara, GaAs emission from

- GaInP/Er,O-codoped GaAs/GaInP laser diodes grown by organometallic vapor phase epitaxy, *Physica Status Solidi (c)*, 印刷中, 2008
12. A. Fujita, T. Tokuno, K. Hidaka, K. Fujii, K. Tachibana, H. Ichida, Y. Terai, Y. Kanematsu and Y. Fujiwara, Nonradiative processes at low temperature in Er,O-codoped GaAs grown by organometallic vapor phase epitaxy, *Physica Status Solidi (c)*, 印刷中, 2008
 13. K. Shimada, S. Takemoto, K. Hidaka, Y. Terai, M. Tonouchi, and Y. Fujiwara, Ultrafast photoexcited carrier dynamics in GaAs:Er,O by pump and probe transmission spectroscopy, *Physica Status Solidi (c)*, 印刷中, 2008
 14. K. Yamaoka, Y. Terai and Y. Fujiwara, Effects of RF power on impurity-doped zinc oxide films by plasma-enhanced chemical vapor deposition, *Physica Status Solidi (c)*, 印刷中, 2008
 15. S. Hashimoto, Y. Terai, A. Kakiuchi and Y. Fujiwara, Epitaxial growth of Al-doped β -FeSi₂ thin film on Si(111) substrate by molecular beam epitaxy, *Physica Status Solidi (c)*, 印刷中, 2008

Symposia

1. Handai Nanoscience and Nanotechnology International Symposium 2007